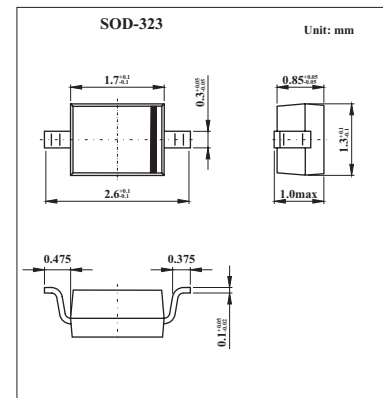


BAP65-03

Features

- High voltage, current controlled
- RF resistor for RF switches
- Low diode capacitance
- Low diode forward resistance (low loss)
- Very low series inductance.



Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Min	Max	Unit
continuous reverse voltage	V _R		30	V
continuous forward current	I _F		100	mA
total power dissipation Ts ≤ 90 °C	P _{tot}		500	mW
storage temperature	T _{stg}	-65	+150	°C
junction temperature	T _j	-65	+150	°C
thermal resistance from junction to soldering point	R _{th j-s}		120	K/W

BAP65-03

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Conditions	Typ	Max	Unit
forward voltage	V _F	I _F = 50 mA	0.95	1.1	V
reverse leakage current	I _R	V _R = 20 V		20	nA
diode capacitance	C _d	V _R = 0; f = 1 MHz	0.65		pF
		V _R = 1 V; f = 1 MHz	0.55	0.9	
		V _R = 3 V; f = 1 MHz	0.5	0.8	
		V _R = 20V; f = 1 MHz	0.375		
diode forward resistance	r _D	I _F = 1 mA; f = 100 MHz; note 1	1		Ω
		I _F = 5 mA; f = 100 MHz; note 1	0.65	0.95	
		I _F = 10 mA; f = 100 MHz; note 1	0.56	0.9	
		I _F = 100 mA; f = 100 MHz	0.35		
isolation	s ₂₁ ²	V _R = 0; f = 900 MHz	10.2		dB
		V _R = 0; f = 1800 MHz	5.8		
		V _R = 0; f = 2450 MHz	4.1		
insertion loss	s ₂₁ ²	V _R = 1; f = 900 MHz	0.1		dB
		V _R = 1; f = 1800 MHz	0.14		
		V _R = 1; f = 2450 MHz	0.18		
insertion loss	s ₂₁ ²	V _R = 5; f = 900 MHz	0.06		dB
		V _R = 5; f = 1800 MHz	0.1		
		V _R = 5; f = 2450 MHz	0.14		
insertion loss	s ₂₁ ²	V _R = 10; f = 900 MHz	0.06		dB
		V _R = 10; f = 1800 MHz	0.1		
		V _R = 10; f = 2450 MHz	0.13		
insertion loss	s ₂₁ ²	V _R = 100; f = 900 MHz	0.05		dB
		V _R = 100; f = 1800 MHz	0.1		
		V _R = 100; f = 2450 MHz	0.14		
charge carrier life time	τ _L	when switched from I _F = 10 mA to I _R = 6 mA; R _L = 100 Ω; measured at I _R = 3 mA	0.17		μs
series inductance	L _s	I _F = 100 mA; f = 100 MHz	1.5		nH

Note

1. Guaranteed on AQL basis: inspection level S4, AQL 1.0.

■ Marking

Marking	D3
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